

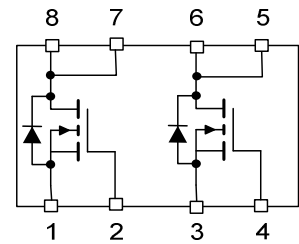
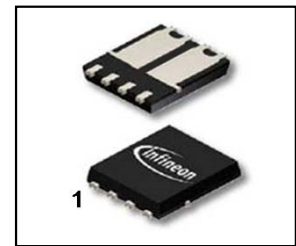
**OptiMOS™-T2 Power-Transistor**

**Product Summary**

$V_{DS}$	100	V
$R_{DS(on),max}^{4)}$	22	mΩ
$I_D$	20	A

**Features**

- Dual N-channel Logic Level - Enhancement mode
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested
- Feasible for automatic optical inspection (AOI)

**PG-TDSON-8-10**


Type	Package	Marking
IPG20N10S4L-22A	PG-TDSON-8-10	4N10L22

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current one channel active <sup>1)</sup>	$I_D$	$T_C=25\text{ °C}$ , $V_{GS}=10\text{V}$	20	A
		$T_C=100\text{ °C}$ , $V_{GS}=10\text{V}^{2)}$	20	
Pulsed drain current <sup>2)</sup> one channel active	$I_{D,pulse}$	-	80	
Avalanche energy, single pulse <sup>2, 4)</sup>	$E_{AS}$	$I_D=10\text{A}$	130	mJ
Avalanche current, single pulse <sup>4)</sup>	$I_{AS}$	-	15	A
Gate source voltage	$V_{GS}$	-	±16	V
Power dissipation one channel active	$P_{tot}$	$T_C=25\text{ °C}$	60	W
Operating and storage temperature	$T_j, T_{stg}$	-	-55 ... +175	°C

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics<sup>2)</sup></b>						
Thermal resistance, junction - case	$R_{thJC}$	-	-	-	2.5	K/W
SMD version, device on PCB	$R_{thJA}$	minimal footprint	-	100	-	
		6cm <sup>2</sup> cooling area <sup>3)</sup>	-	60	-	

**Electrical characteristics, at  $T_j=25^\circ\text{C}$ , unless otherwise specified**

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1\text{mA}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=25\mu\text{A}$	1.1	1.6	2.1	
Zero gate voltage drain current <sup>4)</sup>	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	0.01	1	$\mu\text{A}$
		$V_{DS}=100V, V_{GS}=0V, T_j=125^\circ\text{C}^{2)}$	-	1	100	
Gate-source leakage current <sup>4)</sup>	$I_{GSS}$	$V_{GS}=16V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance <sup>4)</sup>	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=10A$	-	24	28	m $\Omega$
		$V_{GS}=10V, I_D=17A$	-	20	22	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics<sup>2)</sup>**

Input capacitance <sup>4)</sup>	$C_{iss}$	$V_{GS}=0V, V_{DS}=25V,$ $f=1MHz$	-	1350	1755	pF
Output capacitance <sup>4)</sup>	$C_{oss}$		-	450	585	
Reverse transfer capacitance <sup>4)</sup>	$C_{rss}$		-	42	84	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50V, V_{GS}=10V,$ $I_D=20A, R_G=11\Omega$	-	5	-	ns
Rise time	$t_r$		-	3	-	
Turn-off delay time	$t_{d(off)}$		-	30	-	
Fall time	$t_f$		-	18	-	

**Gate Charge Characteristics<sup>2, 4)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=80V, I_D=20A,$ $V_{GS}=0$ to 10V	-	4.3	5.6	nC
Gate to drain charge	$Q_{gd}$		-	4.8	9.6	
Gate charge total	$Q_g$		-	21	27	
Gate plateau voltage	$V_{plateau}$		-	3.2	-	V

**Reverse Diode**

Diode continuous forward current <sup>2)</sup> one channel active	$I_S$	$T_C=25^\circ C$	-	-	20	A
Diode pulse current <sup>2)</sup> one channel active	$I_{S,pulse}$		-	-	80	
Diode forward voltage	$V_{SD}$	$V_{GS}=0V, I_F=17A,$ $T_j=25^\circ C$	-	1.0	1.3	V
Reverse recovery time <sup>2)</sup>	$t_{rr}$	$V_R=50V, I_F=I_S,$ $di_F/dt=100A/\mu s$	-	55	-	ns
Reverse recovery charge <sup>2, 4)</sup>	$Q_{rr}$		-	100	-	nC

<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC} = 2.5K/W$  the chip is able to carry 36A at 25°C.

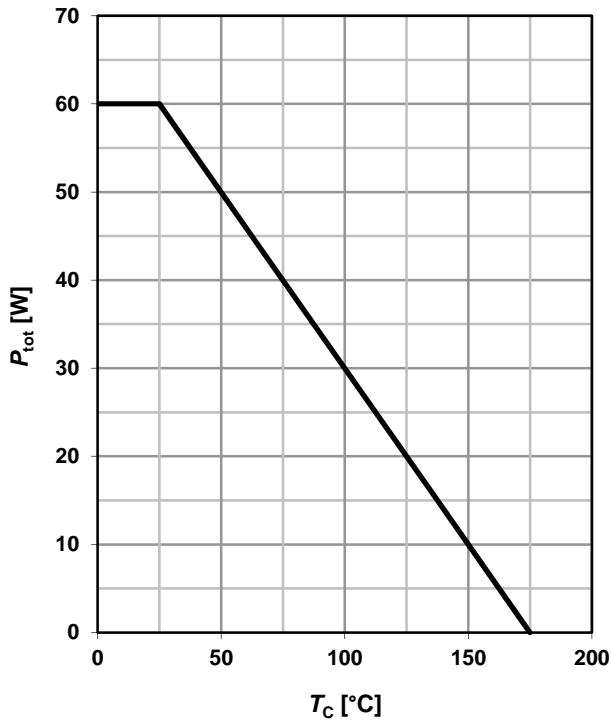
<sup>2)</sup> Specified by design. Not subject to production test.

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>4)</sup> Per channel

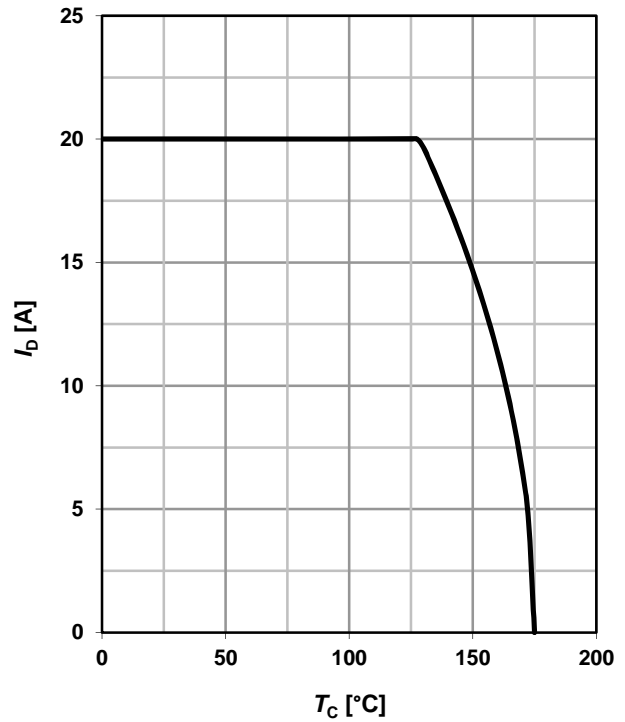
**1 Power dissipation**

$P_{tot}=f(T_C)$ ;  $V_{GS} \geq 6V$ ; one channel active



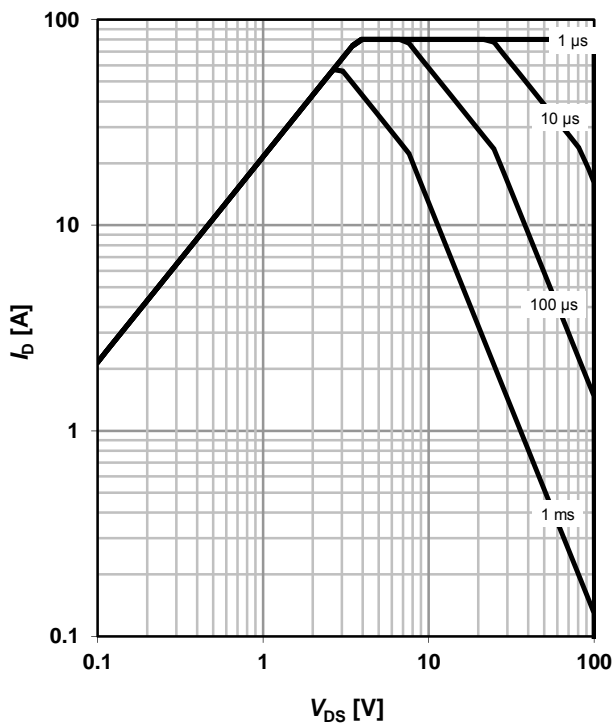
**2 Drain current**

$I_D=f(T_C)$ ;  $V_{GS} \geq 6V$ ; one channel active



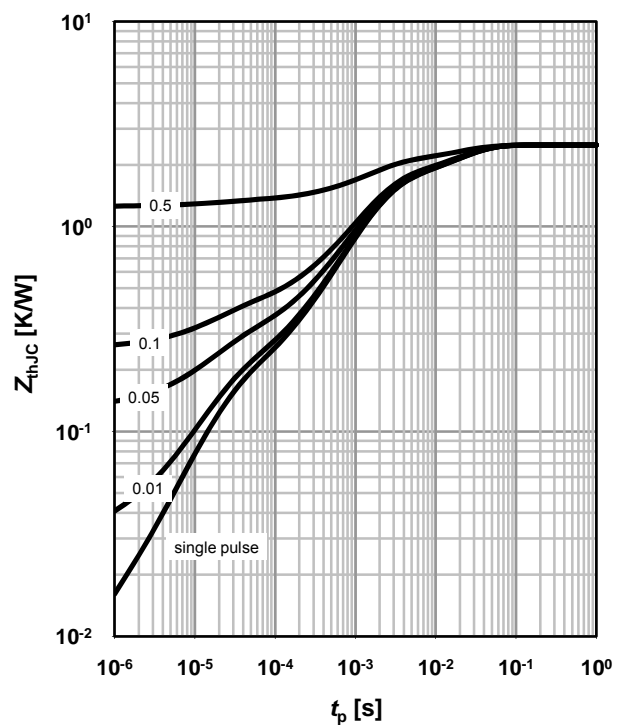
**3 Safe operating area**

$I_D=f(V_{DS})$ ;  $T_C=25^\circ C$ ;  $D=0$ ; one channel active  
parameter:  $t_p$



**4 Max. transient thermal impedance**

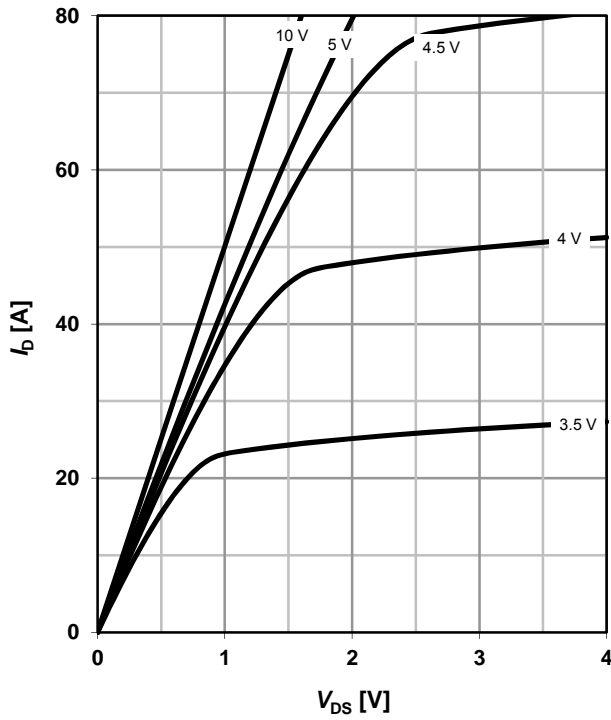
$Z_{thJC}=f(t_p)$   
parameter:  $D=t_p/T$



**5 Typ. output characteristics<sup>5)</sup>**

$I_D=f(V_{DS}); T_j=25^\circ\text{C}$

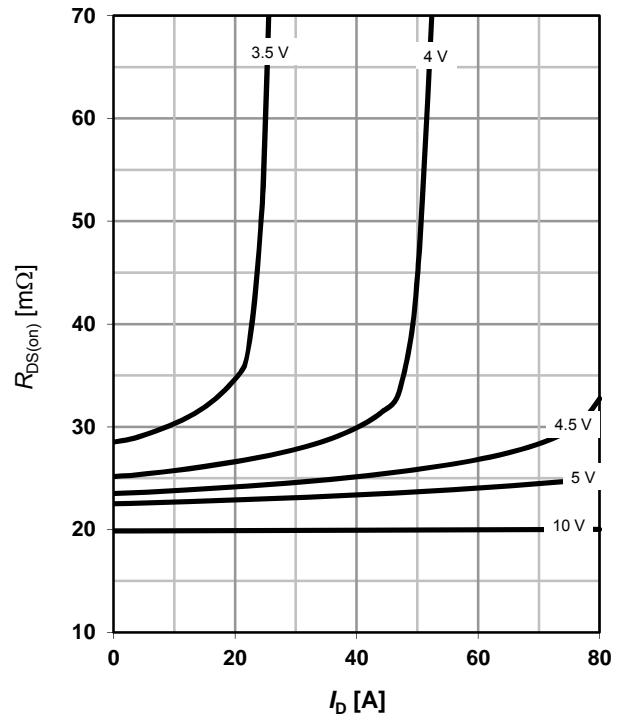
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance<sup>5)</sup>**

$R_{DS(on)}=f(I_D); T_j=25^\circ\text{C}$

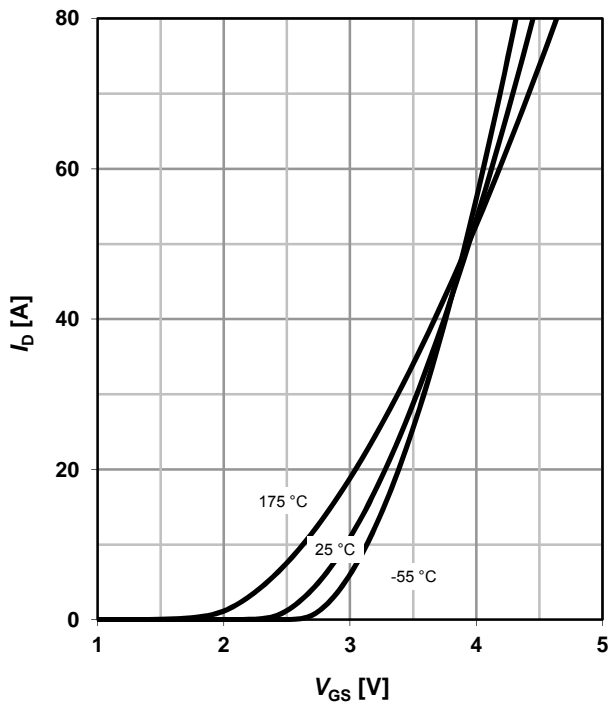
parameter:  $V_{GS}$



**7 Typ. transfer characteristics<sup>5)</sup>**

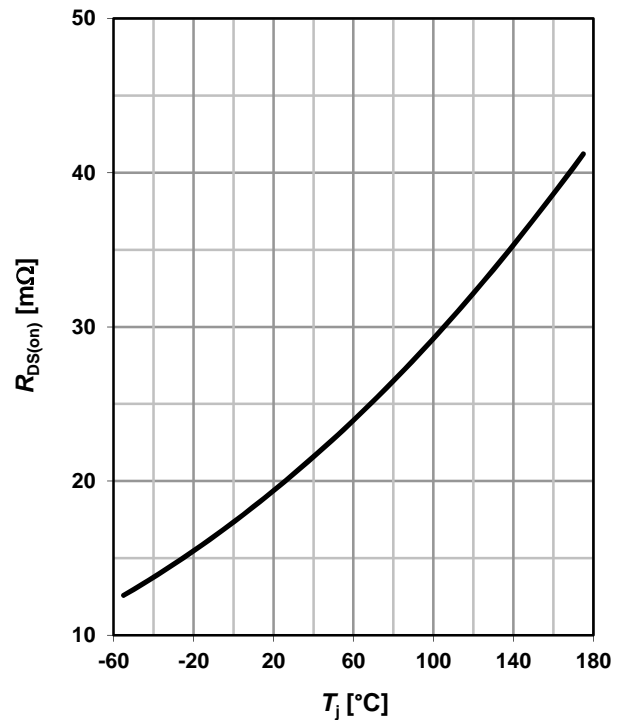
$I_D=f(V_{GS}); V_{DS}=6\text{V}$

parameter:  $T_j$



**8 Typ. drain-source on-state resistance<sup>5)</sup>**

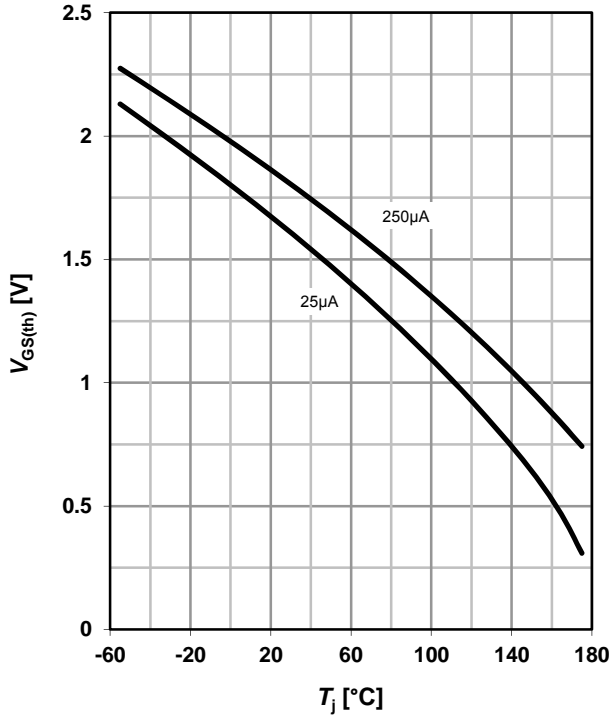
$R_{DS(on)}=f(T_j); I_D=17\text{A}; V_{GS}=10\text{V}$



**9 Typ. gate threshold voltage**

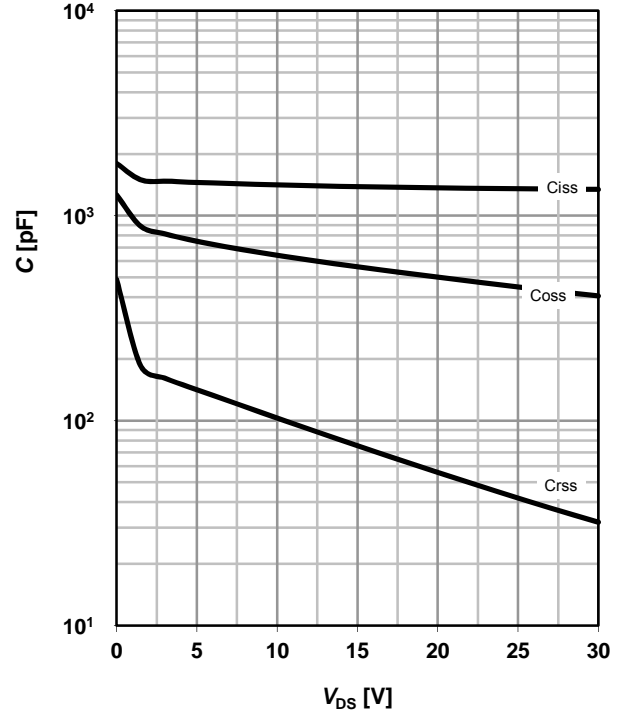
$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}$

parameter:  $I_D$



**10 Typ. Capacitances<sup>5)</sup>**

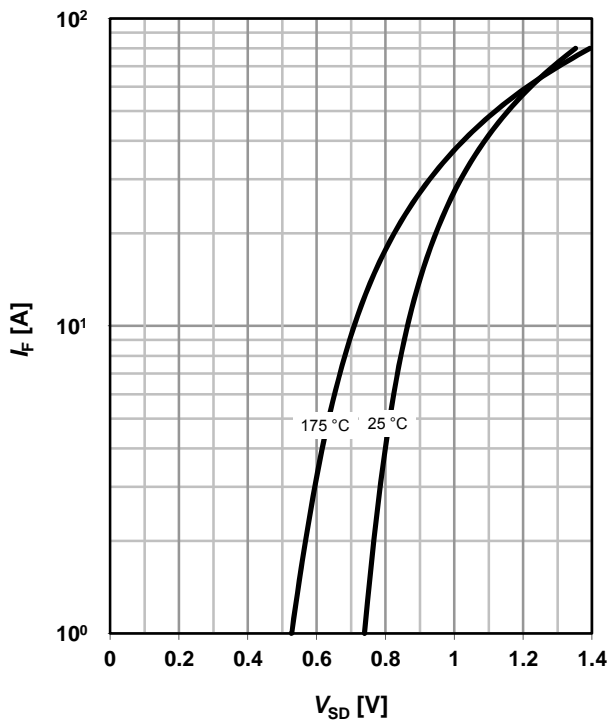
$C=f(V_{DS}); V_{GS}=0V; f=1MHz$



**11 Typical forward diode characteristics<sup>5)</sup>**

$I_F=f(V_{SD})$

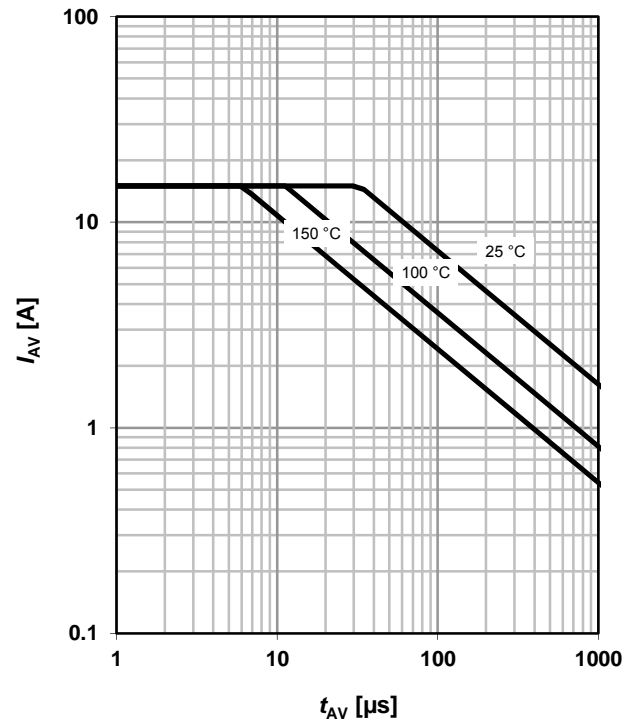
parameter:  $T_j$



**12 Avalanche characteristics<sup>5)</sup>**

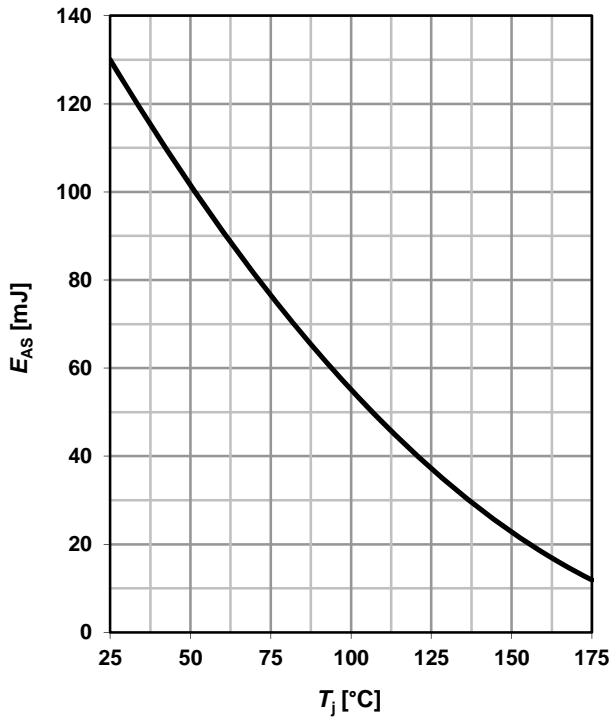
$I_{AS}=f(t_{AV})$

parameter:  $T_{j(start)}$



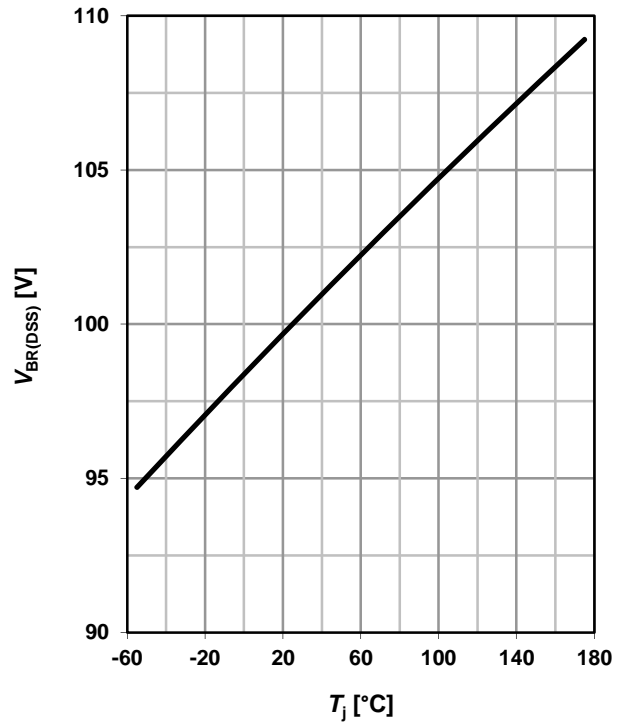
**13 Avalanche energy<sup>5)</sup>**

$E_{AS}=f(T_j), I_D=10A$



**14 Drain-source breakdown voltage**

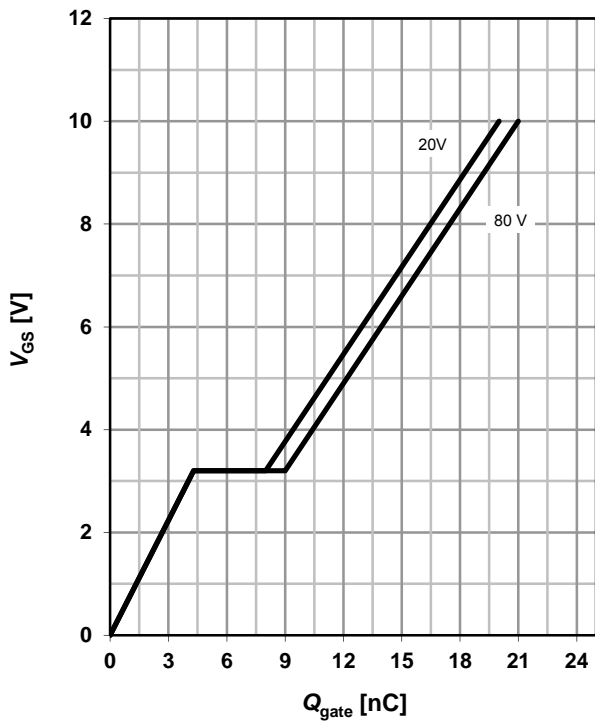
$V_{BR(DSS)}=f(T_j); I_D=1mA$



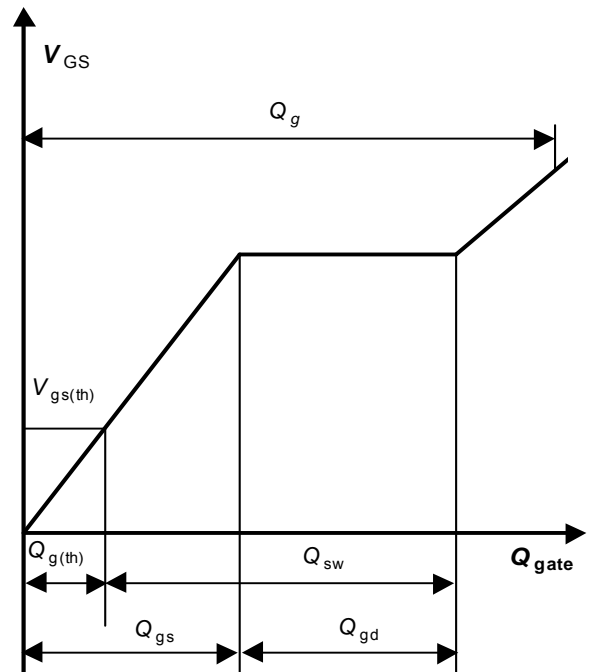
**15 Typ. gate charge<sup>5)</sup>**

$V_{GS}=f(Q_{gate}); I_D=20A$  pulsed

parameter:  $V_{DD}$



**16 Gate charge waveforms**



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## Revision History

Version	Date	Changes
Revision 1.0	04.03.2013	Final Data Sheet